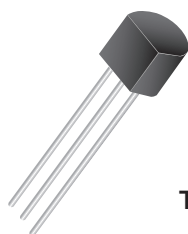
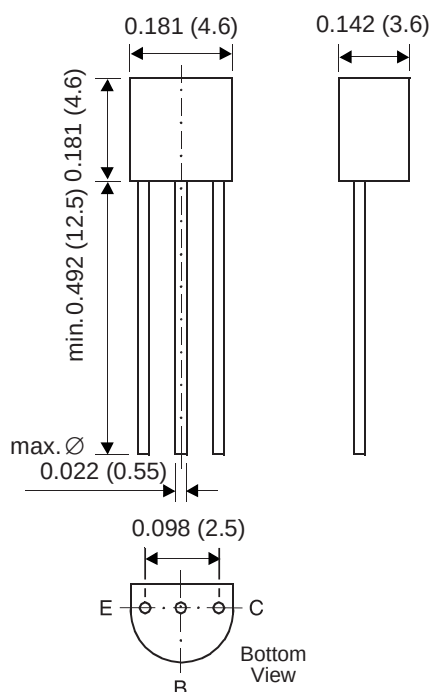




Small Signal Transistor (PNP)



TO-226AA (TO-92)



Dimensions in inches and (millimeters)

Features

- PNP Silicon Epitaxial Planar Transistors for amplifier applications. Especially suitable for low power output stages such as portable radios in class-B push-pull operation.
- Complementary to GS8050xU
- The "x" in the part number can be B, C or D, depending on the current gain.

Mechanical Data

Case: TO-92 Plastic Package

Weight: approx. 0.18g

Packaging Codes/Options:

E6/Bulk – 5K per container, 20K per box

E7/4K per Ammo mag., 20K per box

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-800	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	625 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	200 ⁽¹⁾	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_S	-55 to +150	$^\circ\text{C}$

Note:

(1) Valid provided that leads are kept at ambient temperature at a distance of 2mm from case

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DC Current Gain	h _{FE}	V _{CE} = −1V, I _C = −5mA	45	135	—	—
Current Gain Group B C D		V _{CE} = −1V, I _C = −100mA	85	—	160	
			120	—	200	
			160	—	300	
		V _{CE} = −1V, I _C = −800mA	—	30	—	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = −2mA, I _B = 0	−25	—	—	V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C = −100μA, I _E = 0	−40	—	—	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = −100μA, I _C = 0	−6	—	—	V
Collector Cut-off Current	I _{CBO}	V _{CB} = −35V, I _E = 0	—	—	−100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = −6V, I _C = 0	—	—	−100	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = −800mA, I _B = −80mA	—	−0.51	—	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = −800mA, I _B = −80mA	—	−1.25	—	V
Base-Emitter ON Voltage	V _{BE(on)}	V _{CE} = −1V, I _C = −10mA	—	−0.66	−1.0	V
Output Capacitance	C _{OB}	V _{CB} = −10V, I _E = 0 f = 1 MHz	—	15	—	pF
Gain-Bandwidth Product	f _T	V _{CE} = −10V, I _C = −50mA	—	100	—	MHz